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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

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NPN SILICON HIGH FREQUENCY TRANSISTOR

FEATURES

• SMALL PACKAGE STYLE:

2 NE681 Die in a 2 mm x 1.25 mm package

• LOW NOISE FIGURE:

NF = 1.4 dB TYP at 1 GHz

· HIGH GAIN:

 $|S_{21}E|^2 = 12 dB TYP at 1 GHz$

• **HIGH GAIN BANDWIDTH:** ft = 7 GHz

LOW CURRENT OPERATION

DESCRIPTION

The UPA812T is two NPN high frequency silicon epitaxial transistors encapsulated in an ultra small 6 pin SMT package. Each transistor is independently mounted and easily configured for either dual transistor or cascode operation. The high ft, low voltage bias and small size make this device suited for various hand-held wireless applications.

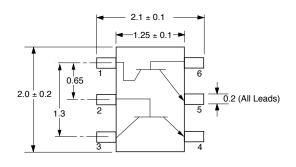
ABSOLUTE MAXIMUM RATINGS¹ (TA = 25°C)

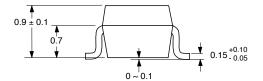
SYMBOLS	PARAMETERS	UNITS	RATINGS
Vсво	Collector to Base Voltage	V	20
VCEO	Collector to Emitter Voltage	V	10
VEBO	Emitter to Base Voltage	V	1.5
Ic	Collector Current	mA	65
PT	Total Power Dissipation 1 Die 2 Die	mW mW	110 200
TJ	Junction Temperature	°C	150
Тѕтс	Storage Temperature	°C	-65 to +150

Note: 1. Operation in excess of any one of these parameters may result in permanent damage.

OUTLINE DIMENSIONS (Units in mm)

PACKAGE OUTLINE S06 (Top View)





PIN OUT

- 1. Collector Transistor 1
- 2. Base Transistor 2
- 3. Collector Transistor 2
- 4. Emitter Transistor 2
- 5. Emitter Transistor 1
- 6. Base Transistor 1

Note

Pin 3 is identified with a circle on the bottom of the package.

ELECTRICAL CHARACTERISTICS (TA = 25°C)

PART NUMBER PACKAGE OUTLINE			UPA812T S06		
SYMBOLS	PARAMETERS AND CONDITIONS	UNITS	MIN	TYP	MAX
Ісво	Collector Cutoff Current at VcB = 10 V, IE = 0	μА			0.8
IEBO	Emitter Cutoff Current at VEB = 1 V, IC = 0	μА			0.8
hFE ¹	Forward Current Gain at VcE = 3 V, Ic = 7 mA		70	100	240
fτ	Gain Bandwidth at VcE = 3 V, Ic = 7 mA, f = 1 GHz	GHz	4.5	7.0	
Cre ²	Feedback Capacitance at VcB = 3 V, IE = 0, f = 1 MHz	pF			0.9
IS21El ²	Insertion Power Gain at VcE = 3 V, Ic = 7 mA, f = 1 GHz	dB	10	12	
NF	Noise Figure at VcE = 3 V, Ic = 7 mA, f = 1 GHz	dB		1.4	1.7
hFE1/hFE2	hFE Ratio: hFE1 = Smaller Value of Q1, or Q2 hFE2 = Larger Value of Q1 or Q2		0.85		

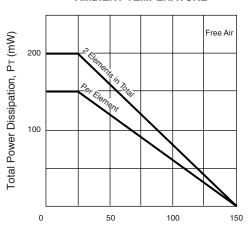
Notes: 1. Pulsed measurement, pulse width \leq 350 μ s, duty cycle \leq 2 %.

2. The emitter terminal should be connected to the ground terminal of the 3 terminal capacitance bridge.

For Tape and Reel version use part number UPA812T-T1, 3K per reel.

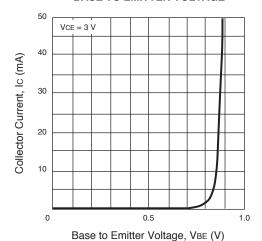
TYPICAL PERFORMANCE CURVES (TA = 25°C)

TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE

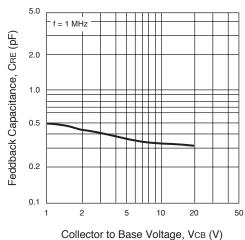


Ambient Temperature, Ta (°C)

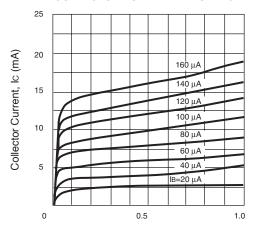
COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE



FEEDBACK CAPACITANCE vs. COLLECTOR TO BASE VOLTAGE

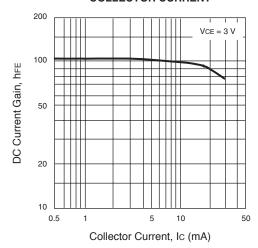


COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE

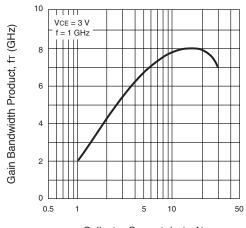


Collector to Emitter Voltage, VcE (V)

DC CURRENT GAIN vs. COLLECTOR CURRENT



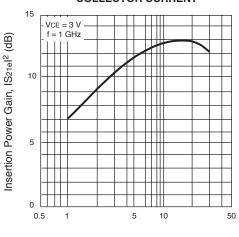
GAIN BANDWIDTH PRODUCT vs. COLLECTOR CURRENT



Collector Current, Ic (mA)

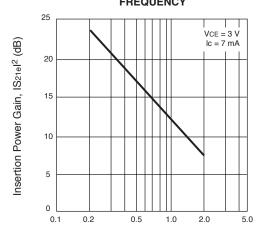
TYPICAL PERFORMANCE CURVES (TA = 25°C)

INSERTION POWER GAIN vs. COLLECTOR CURRENT



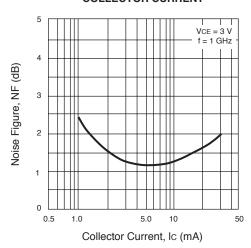
Collector Current, Ic (mA)

INSERTION POWER GAIN vs. FREQUENCY



Frequency, f (GHz)

NOISE FIGURE vs. COLLECTOR CURRENT



ORDERING INFORMATION

PART NUMBER	QUANTITY	PACKAGING	
UPA812T-T1-A	3000	Tape & Reel	